

CMKD3003DO

SURFACE MOUNT
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE SILICON
SWITCHING DIODES

ULTRAmulti™



SOT-363 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD3003DO contains two (2) Isolated Opposing Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmulti™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C303

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage
Average Rectified Current
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, t_p=1.0μs
Peak Forward Surge Current, t_p=1.0s
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R
I_O
I_F
I_{FRM}
I_{FSM}
I_{FSM}
P_D
T_J, T_{stg}
Θ_{JA}

UNITS

V
mA
mA
mA
A
A
mW
°C
°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =125V		1.0	nA
I _R	V _R =125V, T _A =150°C		3.0	μA
I _R	V _R =180V		10	nA
I _R	V _R =180V, T _A =150°C		5.0	μA
BV _R	I _R =5.0μA	200		V
V _F	I _F =1.0mA	0.62	0.72	V
V _F	I _F =10mA	0.72	0.83	V
V _F	I _F =50mA	0.80	0.89	V
V _F	I _F =100mA	0.83	0.93	V
V _F	I _F =200mA	0.87	1.10	V
V _F	I _F =300mA	0.90	1.15	V
C _T	V _R =0, f=1.0MHz		4.0	pF

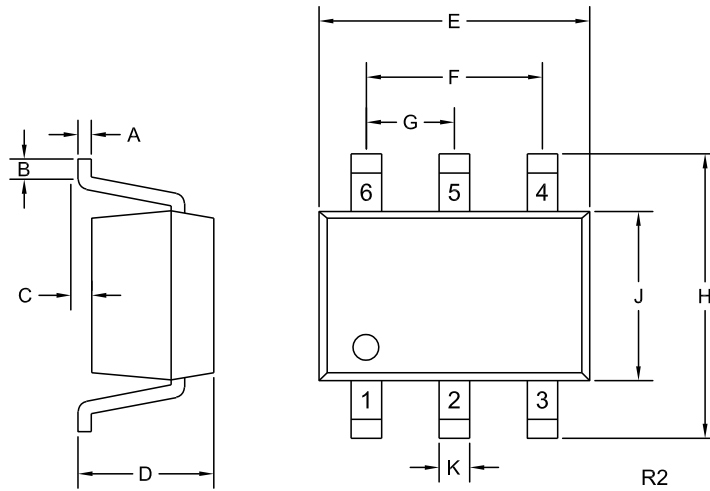
R0 (19-September 2011)

CMKD3003DO

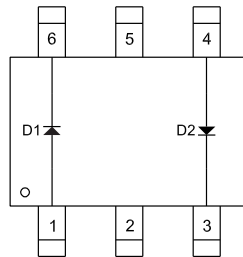
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SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

MARKING CODE: C303

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R0 (19-September 2011)